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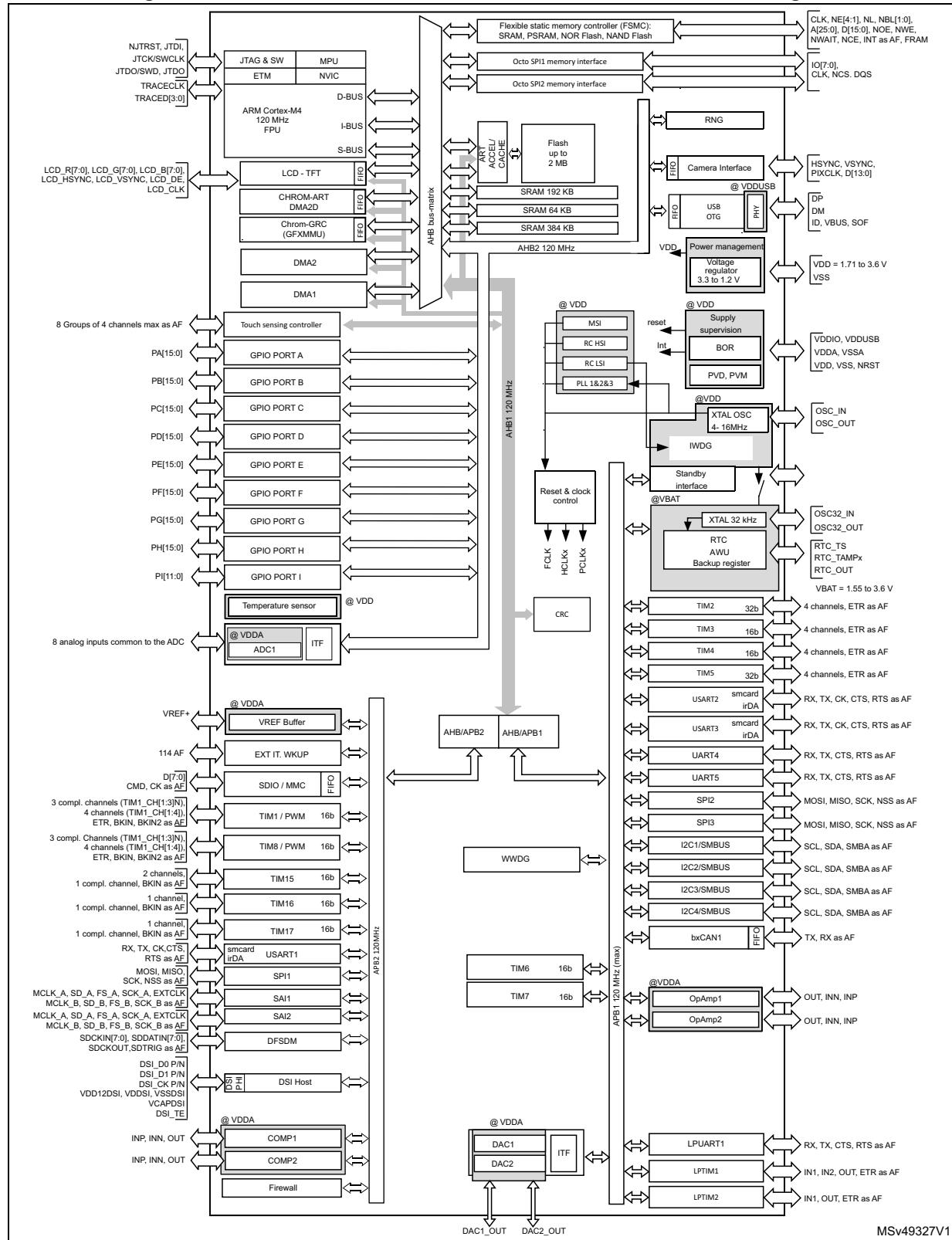
"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

#### Applications of "[Embedded - Microcontrollers](#)"

##### Details

Product Status	Active
Core Processor	ARM® Cortex®-M4
Core Size	32-Bit Single-Core
Speed	120MHz
Connectivity	CANbus, EBI/EMI, I²C, IrDA, LINbus, MMC/SD, SAI, SPI, UART/USART, USB OTG
Peripherals	Brown-out Detect/Reset, DMA, LCD, POR, PWM, WDT
Number of I/O	112
Program Memory Size	2MB (2M x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	640K x 8
Voltage - Supply (Vcc/Vdd)	1.71V ~ 3.6V
Data Converters	A/D 16x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	144-LQFP
Supplier Device Package	144-LQFP (20x20)
Purchase URL	<a href="https://www.e-xfl.com/product-detail/stmicroelectronics/stm32l4r9zit6">https://www.e-xfl.com/product-detail/stmicroelectronics/stm32l4r9zit6</a>

Figure 1. STM32L4R5xx, STM32L4R7xx and STM32L4R9xx block diagram



Note: AF: alternate function on I/O pins.

### 3.19 Analog-to-digital converter (ADC)

The device embeds a successive approximation analog-to-digital converters with the following features:

- 12-bit native resolution, with built-in calibration
- 5.33 Msps maximum conversion rate with full resolution
  - Down to 18.75 ns sampling time
  - Increased conversion rate for lower resolution (up to 8.88 Msps for 6-bit resolution)
- Up to 16 external channels
- 5 internal channels: internal reference voltage, temperature sensor, VBAT/3, DAC1 and DAC2 outputs
- One external reference pin is available on some package, allowing the input voltage range to be independent from the power supply
- Single-ended and differential mode inputs
- Low-power design
  - Capable of low-current operation at low conversion rate (consumption decreases linearly with speed)
  - Dual clock domain architecture: ADC speed independent from CPU frequency
- Highly versatile digital interface
  - Single-shot or continuous/discontinuous sequencer-based scan mode: 2 groups of analog signals conversions can be programmed to differentiate background and high-priority real-time conversions
  - Each ADC support multiple trigger inputs for synchronization with on-chip timers and external signals
  - Results stored into a data register or in RAM with DMA controller support
  - Data pre-processing: left/right alignment and per channel offset compensation
  - Built-in oversampling unit for enhanced SNR
  - Channel-wise programmable sampling time
  - Analog watchdog for automatic voltage monitoring, generating interrupts and trigger for selected timers
  - Hardware assistant to prepare the context of the injected channels to allow fast context switching

#### 3.19.1 Temperature sensor

The temperature sensor (TS) generates a voltage  $V_{TS}$  that varies linearly with temperature. The temperature sensor is internally connected to the ADC1\_IN17 input channels which is used to convert the sensor output voltage into a digital value.

The sensor provides good linearity but it has to be calibrated to obtain good overall accuracy of the temperature measurement. As the offset of the temperature sensor varies from chip to chip due to process variation, the uncalibrated internal temperature sensor is suitable for applications that detect temperature changes only.

To improve the accuracy of the temperature sensor measurement, each device is individually factory-calibrated by ST. The temperature sensor factory calibration data are stored by ST in the system memory area, accessible in read-only mode.

### 3.31 Real-time clock (RTC) and backup registers

The RTC is an independent BCD timer/counter. It supports the following features:

- Calendar with subsecond, seconds, minutes, hours (12 or 24 format), week day, date, month, year, in BCD (binary-coded decimal) format
- Automatic correction for 28, 29 (leap year), 30, and 31 days of the month
- Two programmable alarms
- On-the-fly correction from 1 to 32767 RTC clock pulses. This can be used to synchronize it with a master clock
- Reference clock detection: a more precise second source clock (50 or 60 Hz) can be used to enhance the calendar precision
- Digital calibration circuit with 0.95 ppm resolution, to compensate for quartz crystal inaccuracy
- Three anti-tamper detection pins with programmable filter
- Timestamp feature which can be used to save the calendar content. This function can be triggered by an event on the timestamp pin, or by a tamper event, or by a switch to VBAT mode
- 17-bit auto-reload wakeup timer (WUT) for periodic events with programmable resolution and period

The RTC and the 32 backup registers are supplied through a switch that takes power either from the  $V_{DD}$  supply when present or from the VBAT pin.

The backup registers are 32-bit registers used to store 128 bytes of user application data when  $V_{DD}$  power is not present. They are not reset by a system or power reset, or when the device wakes up from standby or Shutdown mode.

The RTC clock sources can be:

- A 32.768 kHz external crystal (LSE)
- An external resonator or oscillator (LSE)
- The internal low-power RC oscillator (LSI, with typical frequency of 32 kHz)
- The high-speed external clock (HSE) divided by 32

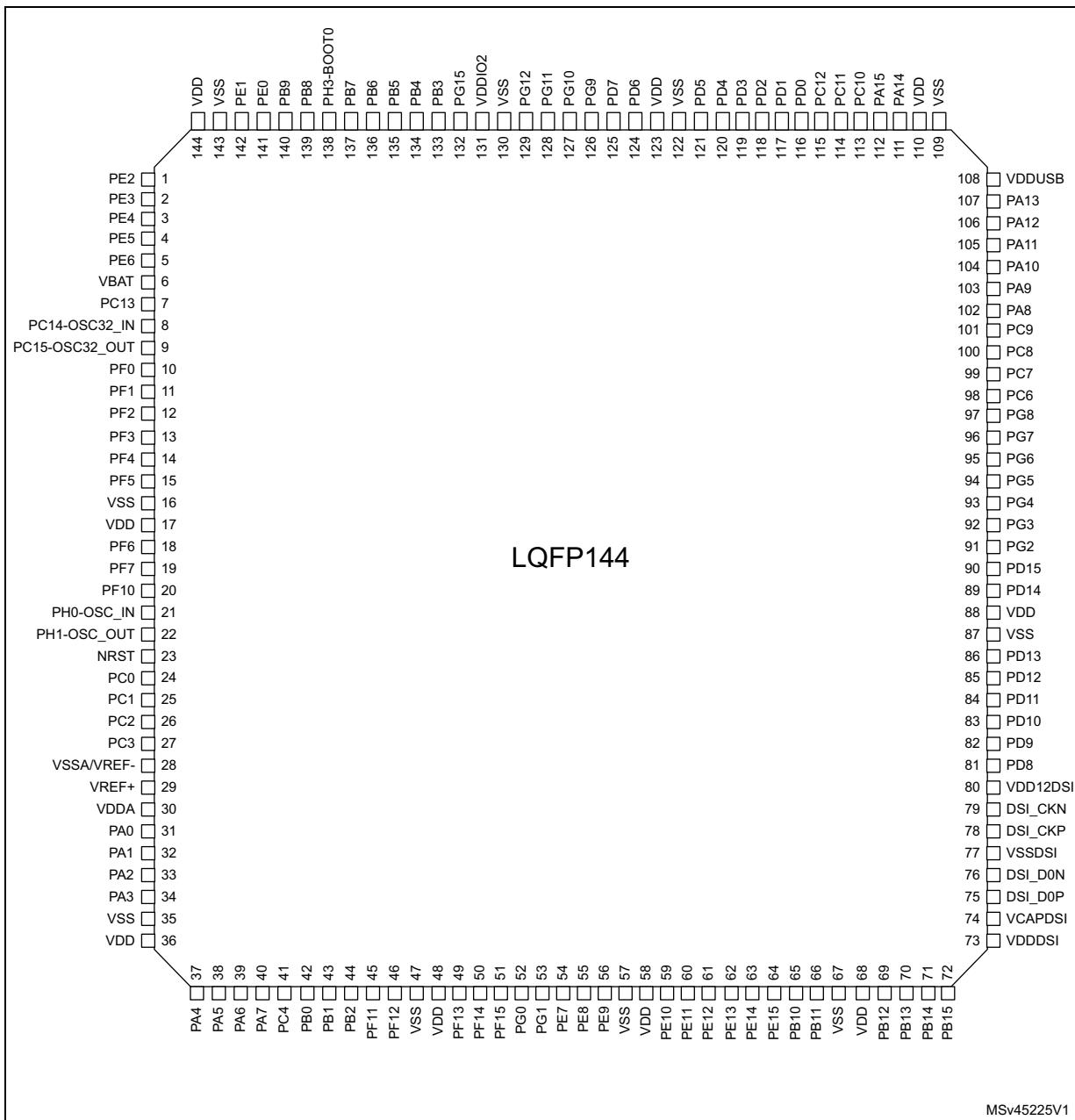
The RTC is functional in VBAT mode and in all low-power modes when it is clocked by the LSE. When clocked by the LSI, the RTC is not functional in VBAT mode, but is functional in all low-power modes except Shutdown mode.

All RTC events (alarm, wake-up timer, Timestamp or Tamper) can generate an interrupt and wakeup the device from the low-power modes.

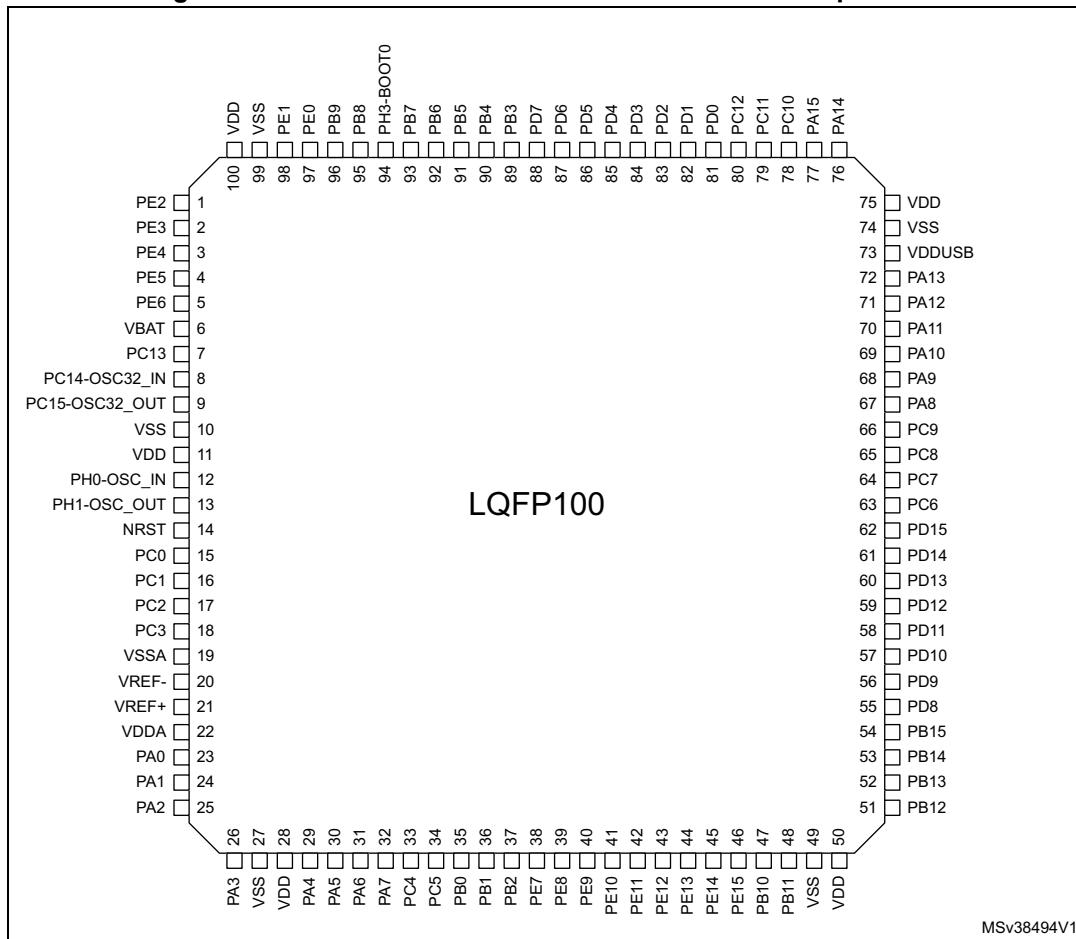
### 3.32 Inter-integrated circuit interface (I<sup>2</sup>C)

The device embeds four I<sup>2</sup>C. Refer to [Table 11: I<sup>2</sup>C implementation](#) for the features implementation.

The I<sup>2</sup>C bus interface handles communications between the microcontroller and the serial I<sup>2</sup>C bus. It controls all I<sup>2</sup>C bus-specific sequencing, protocol, arbitration and timing.

Figure 13. STM32L4R9xx LQFP144 pinout<sup>(1)</sup>

1. The above figure shows the package top view.

Figure 21. STM32L4R5xx and STM32L4R7xx LQFP100 pinout<sup>(1)</sup>

1. The above figure shows the package top view.

Table 15. STM32L4Rxxx pin definitions (continued)

Pin number														Pin name (function after reset)	Pin type	I/O structure	Notes	Alternate functions	Additional functions
STM32L4R5xxx, STM32L4R7xxx							STM32L4R9xxx												
29	J4	J4	40	40	K9	L3	L3	27	37	K4	K9	K9	N2	PA4	I/O	TT_a	-	OCTOSPI_M1_NCS, SPI1_NSS, SPI3_NSS, USART2_CK, DCMI_HSYNC, SAI1_FS_B, LPTIM2_OUT, EVENTOUT	ADC1_IN9, DAC1_OUT1
30	K4	K4	41	41	G8	K4	K4	28	38	L4	G8	G8	L3	PA5	I/O	TT_a	-	TIM2_CH1, TIM2_ETR, TIM8_CH1N, SPI1_SCK, LPTIM2_ETR, EVENTOUT	ADC1_IN10, DAC1_OUT2
31	L4	L4	42	42	J8	M4	M4	29	39	J4	J8	J8	L4	PA6	I/O	FT_a	-	TIM1_BKIN, TIM3_CH1, TIM8_BKIN, DCMI_PIXCLK, SPI1_MISO, USART3_CTS_NSS, LPUART1_CTS, OCTOSPI_M1_IO3, TIM16_CH1, EVENTOUT	OPAMP2_VINP, ADC1_IN11

Table 15. STM32L4Rxxx pin definitions (continued)

Pin number														Pin name (function after reset)	Pin type	I/O structure	Notes	Alternate functions	Additional functions		
STM32L4R5xxx, STM32L4R7xxx							STM32L4R9xxx														
LQFP100	BGA132_SMPS	BGA132	LQFP144_SMPS	LQFP144	WL CSP144	UFBGA169_SMPS	UFBGA169	LQFP100	LQFP144	UFBGA144	WL CSP144_SMPS	WL CSP144	UFBGA169								
45	M11	M11	67	67	H5	K8	K8	42	63	M10	H5	H5	K7	PE14	I/O	FT	-	TIM1_CH4, TIM1_BKIN2, SPI1_MISO, OCTOSPI_M_P1_IO2, LCD_G7, FMC_D11, EVENTOUT	-		
46	M12	M12	68	68	K4	J8	J8	43	64	K8	K4	K4	J7	PE15	I/O	FT	-	TIM1_BKIN, SPI1_MOSI, OCTOSPI_M_P1_IO3, LCD_R2, FMC_D12, EVENTOUT	-		
47	L10	L10	69	69	L4	N9	N9	44	65	L9	L4	L4	N9	PB10	I/O	FT_f1	-	TIM2_CH3, I2C4_SCL, I2C2_SCL, SPI2_SCK, DFSDM1_DATIN7, USART3_TX, LPUART1_RX, TSC_SYNC, OCTOSPI_M_P1_CLK, COMP1_OUT, SAI1_SCK_A, EVENTOUT	-		

Table 16. Alternate function AF0 to AF7<sup>(1)</sup> (continued)

Port		AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7
		OTG_FS/ SYS_AF	TIM1/2/5/8/L PTIM1	TIM1/2/3/4/ 5	SPI2/SAI1/I2C4/U SART2/OTG_FS/T IM1/8/OCTOSPI _P1	I2C1/2/3/4/DC MI	SPI1/2/3/I2C4/DFS DM1/DCMI/OCTOS PIM_P1/2	SPI3/I2C3/DFS DM1/COMP1/O CTOSPI_P2	USART1/2/3
Port D	PD0	-	-	-	-	-	SPI2_NSS	DFSDM1_DATIN7	-
	PD1	-	-	-	-	-	SPI2_SCK	DFSDM1_CKIN7	-
	PD2	TRACED2	-	TIM3_ETR	-	-	-	-	USART3_RTS_DE
	PD3	-	-	-	SPI2_SCK	DCMI_D5	SPI2_MISO	DFSDM1_DATIN0	USART2_CTS_NSS
	PD4	-	-	-	-	-	SPI2_MOSI	DFSDM1_CKIN0	USART2_RTS_DE
	PD5	-	-	-	-	-	-	-	USART2_TX
	PD6	-	-	-	SAI1_D1	DCMI_D10	SPI3_MOSI	DFSDM1_DATIN1	USART2_RX
	PD7	-	-	-	-	-	-	DFSDM1_CKIN1	USART2_CK
	PD8	-	-	-	-	-	-	-	USART3_TX
	PD9	-	-	-	-	-	-	-	USART3_RX
	PD10	-	-	-	-	-	-	-	USART3_CK
	PD11	-	-	-	-	I2C4_SMBA	-	-	USART3_CTS_NSS
	PD12	-	-	TIM4_CH1	-	I2C4_SCL	-	-	USART3_RTS_DE
	PD13	-	-	TIM4_CH2	-	I2C4_SDA	-	-	-
	PD14	-	-	TIM4_CH3	-	-	-	-	-
	PD15	-	-	TIM4_CH4	-	-	-	-	-

Table 16. Alternate function AF0 to AF7<sup>(1)</sup> (continued)

Port		AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7
		OTG_FS/ SYS_AF	TIM1/2/5/8/L PTIM1	TIM1/2/3/4/ 5	SPI2/SAI1/I2C4/U SART2/OTG_FS/T IM1/8/OCTOSPIM _P1	I2C1/2/3/4/DC MI	SPI1/2/3/I2C4/DFS DM1/DCMI/OCTOS PIM_P1/2	SPI3/I2C3/DFS DM1/COMP1/O CTOSPIM_P2	USART1/2/3
Port I	PI0	-	-	TIM5_CH4	OCTOSPIM_P1_IO5	-	SPI2_NSS	-	-
	PI1	-	-	-	-	-	SPI2_SCK	-	-
	PI2	-	-	-	TIM8_CH4	-	SPI2_MISO	-	-
	PI3	-	-	-	TIM8_ETR	-	SPI2_MOSI	-	-
	PI4	-	-	-	TIM8_BKIN	-	-	-	-
	PI5	-	-	-	TIM8_CH1	-	OCTOSPIM_P2_NCS	-	-
	PI6	-	-	-	TIM8_CH2	-	OCTOSPIM_P2_CLK	-	-
	PI7	-	-	-	TIM8_CH3	-	-	-	-
	PI8	-	-	-	-	-	OCTOSPIM_P2_NCS	-	-
	PI9	-	-	-	-	-	OCTOSPIM_P2_IO2	-	-
	PI10	-	-	-	-	-	OCTOSPIM_P2_IO1	-	-
	PI11	-	-	-	-	-	OCTOSPIM_P2_IO0	-	-

1. Refer to [Table 17](#) for AF8 to AF15.

Table 17. Alternate function AF8 to AF15<sup>(1)</sup> (continued)

Port		AF8	AF9	AF10	AF11	AF12	AF13	AF14	AF15
		UART4/5/ LPUART1/ CAN2	CAN1/TSC	OTG_FS/DCMI/ OCTOSPI_P1/P2	LCD	SDMMC/ COMP1/2/ FMC	SAI1/2	TIM2/15/16/17/ LPTIM2	EVENOUT
Port B	PB0	-	-	OCTOSPI_M_P1_IO1	-	COMP1_OUT	SAI1_EXTCLK	-	EVENTOUT
	PB1	LPUART1_RTS_DE	-	OCTOSPI_M_P1_IO0	-	-	-	LPTIM2_IN1	EVENTOUT
	PB2	-	-	OCTOSPI_M_P1_DQS	LCD_B1	-	-	-	EVENTOUT
	PB3	-	-	OTG_FS_CRS_SYNC	-	-	SAI1_SCK_B	-	EVENTOUT
	PB4	UART5_RTS_DE	TSC_G2_IO1	DCMI_D12	-	-	SAI1_MCLK_B	TIM17_BKIN	EVENTOUT
	PB5	UART5_CTS	TSC_G2_IO2	DCMI_D10	-	COMP2_OUT	SAI1_SD_B	TIM16_BKIN	EVENTOUT
	PB6	-	TSC_G2_IO3	DCMI_D5	-	TIM8_BKIN2	SAI1_FS_B	TIM16_CH1N	EVENTOUT
	PB7	UART4_CTS	TSC_G2_IO4	DCMI_VSYNC	DSI_TE	FMC_NL	TIM8_BKIN	TIM17_CH1N	EVENTOUT
	PB8	SDMMC1_CKIN	CAN1_RX	DCMI_D6	LCD_B1	SDMMC1_D4	SAI1_MCLK_A	TIM16_CH1	EVENTOUT
	PB9	SDMMC1_CDIR	CAN1_TX	DCMI_D7	-	SDMMC1_D5	SAI1_FS_A	TIM17_CH1	EVENTOUT
	PB10	LPUART1_RX	TSC_SYNC	OCTOSPI_M_P1_CLK	-	COMP1_OUT	SAI1_SCK_A	-	EVENTOUT
	PB11	LPUART1_TX	-	OCTOSPI_M_P1_NCS	DSI_TE	COMP2_OUT	-	-	EVENTOUT
	PB12	LPUART1_RT_S_DE	TSC_G1_IO1	-	-	-	SAI2_FS_A	TIM15_BKIN	EVENTOUT
	PB13	LPUART1_CTS	TSC_G1_IO2	-	-	-	SAI2_SCK_A	TIM15_CH1N	EVENTOUT
	PB14	-	TSC_G1_IO3	-	-	-	SAI2_MCLK_A	TIM15_CH1	EVENTOUT
	PB15	-	TSC_G1_IO4	-	-	-	SAI2_SD_A	TIM15_CH2	EVENTOUT

Table 17. Alternate function AF8 to AF15<sup>(1)</sup> (continued)

Port		AF8	AF9	AF10	AF11	AF12	AF13	AF14	AF15
		UART4/5/ LPUART1/ CAN2	CAN1/TSC	OTG_FS/DCMI/ OCTOSPI_P1/P2	LCD	SDMMC/ COMP1/2/ FMC	SAI1/2	TIM2/15/16/17/ LPTIM2	EVENOUT
Port C	PC0	LPUART1_RX	-	-	-	-	SAI2_FS_A	LPTIM2_IN1	EVENTOUT
	PC1	LPUART1_TX	-	OCTOSPIM_P1_IO4	-	-	SAI1_SD_A	-	EVENTOUT
	PC2	-	-	OCTOSPIM_P1_IO5	-	-	-	-	EVENTOUT
	PC3	-	-	OCTOSPIM_P1_IO6	-	-	SAI1_SD_A	LPTIM2_ETR	EVENTOUT
	PC4	-	-	OCTOSPIM_P1_IO7	-	-	-	-	EVENTOUT
	PC5	-	-	-	-	-	-	-	EVENTOUT
	PC6	SDMMC1_D0DIR	TSC_G4_IO1	DCMI_D0	LCD_R0	SDMMC1_D6	SAI2_MCLK_A	-	EVENTOUT
	PC7	SDMMC1_D123DIR	TSC_G4_IO2	DCMI_D1	LCD_R1	SDMMC1_D7	SAI2_MCLK_B	-	EVENTOUT
	PC8	-	TSC_G4_IO3	DCMI_D2	-	SDMMC1_D0	-	-	EVENTOUT
	PC9	-	TSC_G4_IO4	OTG_FS_NOE	-	SDMMC1_D1	SAI2_EXTCLK	TIM8_BKIN2	EVENTOUT
	PC10	UART4_TX	TSC_G3_IO2	DCMI_D8	-	SDMMC1_D2	SAI2_SCK_B	-	EVENTOUT
	PC11	UART4_RX	TSC_G3_IO3	DCMI_D4	-	SDMMC1_D3	SAI2_MCLK_B	-	EVENTOUT
	PC12	UART5_TX	TSC_G3_IO4	DCMI_D9	-	SDMMC1_CK	SAI2_SD_B	-	EVENTOUT
	PC13	-	-	-	-	-	-	-	EVENTOUT
	PC14	-	-	-	-	-	-	-	EVENTOUT
	PC15	-	-	-	-	-	-	-	EVENTOUT

**Table 18. STM32L4R5xx, STM32L4R7xx and STM32L4R9xx memory map and peripheral register boundary addresses<sup>(1)</sup> (continued)**

Bus	Boundary address	Size (bytes)	Peripheral
AHB1	0x4002 F000 - 0x47FF FFFF	~127 MB	Reserved
	0x4002 C000 - 0x4002 EFFF	1KB	GFXMMU
	0x4002 BC00 - 0x4002 BBFF	1 KB	Reserved
	0x4002 B000 - 0x4002 BBFF	3 KB	DMA2D
	0x4002 4400 - 0x4002 AFFF	26 KB	Reserved
	0x4002 4000 - 0x4002 43FF	1 KB	TSC
	0x4002 3400 - 0x4002 3FFF	1 KB	Reserved
	0x4002 3000 - 0x4002 33FF	1 KB	CRC
	0x4002 2400 - 0x4002 2FFF	3 KB	Reserved
	0x4002 2000 - 0x4002 23FF	1 KB	FLASH registers
	0x4002 1400 - 0x4002 1FFF	3 KB	Reserved
	0x4002 1000 - 0x4002 13FF	1 KB	RCC
	0x4002 0800 - 0x4002 0FFF	2 KB	Reserved
	0x4002 0400 - 0x4002 07FF	1 KB	DMA2
APB2	0x4001 7400 - 0x4001 FFFF	33 KB	Reserved
	0x4001 6C00 - 0x4001 73FF	1 KB	DSIHOST
	0x4001 6800 - 0x4001 6BFF	1 KB	LCD-TFT
	0x4001 6000 - 0x4001 67FF	2 KB	DFSDM1
	0x4001 5C00 - 0x4001 5FFF	1 KB	Reserved
	0x4001 5800 - 0x4001 5BFF	1 KB	SAI2
	0x4001 5400 - 0x4001 57FF	1 KB	SAI1
	0x4001 4C00 - 0x4001 53FF	2 KB	Reserved
	0x4001 4800 - 0x4001 4BFF	1 KB	TIM17
	0x4001 4400 - 0x4001 47FF	1 KB	TIM16
	0x4001 4000 - 0x4001 43FF	1 KB	TIM15
	0x4001 3C00 - 0x4001 3FFF	1 KB	Reserved
	0x4001 3800 - 0x4001 3BFF	1 KB	USART1
	0x4001 3400 - 0x4001 37FF	1 KB	TIM8
	0x4001 3000 - 0x4001 33FF	1 KB	SPI1
	0x4001 2C00 - 0x4001 2FFF	1 KB	TIM1
	0x4001 2000 - 0x4001 2BFF	3 KB	Reserved

Table 51. Current consumption in VBAT mode

Symbol	Parameter	Conditions		TYP					MAX <sup>(1)</sup>					Unit
		-	V <sub>BAT</sub>	25°C	55°C	85°C	105°C	125°C	25°C	55°C	85°C	105°C	125°C	
IDD(VBAT)	Backup domain supply current	RTC disabled	1.8 V	3.00	27.0	165	495	1350	8.0	67.0	390	1200	3000	nA
			2.4 V	4.00	31.0	190	560	1550	10.0	76.0	440	1300	3300	
			3 V	6.00	43.0	255	750	2000	13.0	91.0	510	1500	3800	
			3.6 V	14.0	83.0	485	1450	4050	34.0	200	1100	3100	8300	
		RTC enabled and clocked by LSE bypassed at 32768 Hz	1.8 V	215	240	390	730	-	-	-	-	-	-	
			2.4 V	305	340	510	900	-	-	-	-	-	-	
			3 V	415	455	680	1200	-	-	-	-	-	-	
			3.6 V	540	595	925	1900	-	-	-	-	-	-	
		RTC enabled and clocked by LSE quartz <sup>(2)</sup>	1.8 V	305	345	510	865	1600	-	-	-	-	-	
			2.4 V	395	440	625	1050	1800	-	-	-	-	-	
			3 V	510	565	805	1350	2300	-	-	-	-	-	
			3.6 V	650	740	1200	2200	4450	-	-	-	-	-	

1. Guaranteed by characterization results, unless otherwise specified.

2. Based on characterization done with a 32.768 kHz crystal (MC306-G-06Q-32.768, manufacturer JFVN) with two 6.8 pF loading capacitors.

Table 61. MSI oscillator characteristics<sup>(1)</sup> (continued)

Symbol	Parameter	Conditions			Min	Typ	Max	Unit	
$\Delta V_{DD(MSI)}^{(2)}$	MSI oscillator frequency drift over $V_{DD}$ (reference is 3 V)	MSI mode	Range 0 to 3	$V_{DD}=1.62\text{ V}$ to 3.6 V	-1.2	-	0.5	%	
				$V_{DD}=2.4\text{ V}$ to 3.6 V	-0.5	-			
			Range 4 to 7	$V_{DD}=1.62\text{ V}$ to 3.6 V	-2.5	-	0.7		
				$V_{DD}=2.4\text{ V}$ to 3.6 V	-0.8	-			
			Range 8 to 11	$V_{DD}=1.62\text{ V}$ to 3.6 V	-5	-	1		
				$V_{DD}=2.4\text{ V}$ to 3.6 V	-1.6	-			
$\Delta f_{SAMPLING(MSI)}^{(2)(6)}$	Frequency variation in sampling mode <sup>(3)</sup>	MSI mode	$T_A = -40$ to 85 °C		-	1	2	%	
			$T_A = -40$ to 125 °C		-	2	4		
P_USB Jitter(MSI) <sup>(6)</sup>	Period jitter for USB clock <sup>(4)</sup>	PLL mode Range 11	for next transition	-	-	-	3.458	ns	
			for paired transition	-	-	-	3.916		
MT_USB Jitter(MSI) <sup>(6)</sup>	Medium term jitter for USB clock <sup>(5)</sup>	PLL mode Range 11	for next transition	-	-	-	2	ns	
			for paired transition	-	-	-	1		
CC jitter(MSI) <sup>(6)</sup>	RMS cycle-to-cycle jitter	PLL mode Range 11	-	-	60	-	ps		
P jitter(MSI) <sup>(6)</sup>	RMS Period jitter	PLL mode Range 11	-	-	50	-	ps		
$t_{SU(MSI)}^{(6)}$	MSI oscillator start-up time	MSI mode Range 11	Range 0	-	-	10	20	us	
			Range 1	-	-	5	10		
			Range 2	-	-	4	8		
			Range 3	-	-	3	7		
			Range 4 to 7	-	-	3	6		
			Range 8 to 11	-	-	2.5	6		
$t_{STAB(MSI)}^{(6)}$	MSI oscillator stabilization time	PLL mode Range 11	10 % of final frequency	-	-	0.25	0.5	ms	
			5 % of final frequency	-	-	0.5	1.25		
			1 % of final frequency	-	-	-	2.5		

### Prequalification trials

Most of the common failures (unexpected reset and program counter corruption) can be reproduced by manually forcing a low state on the NRST pin or the Oscillator pins for 1 second.

To complete these trials, ESD stress can be applied directly on the device, over the range of specification values. When unexpected behavior is detected, the software can be hardened to prevent unrecoverable errors occurring (see application note AN1015).

### Electromagnetic Interference (EMI)

The electromagnetic field emitted by the device are monitored while a simple application is executed (toggling 2 LEDs through the I/O ports). This emission test is compliant with IEC 61967-2 standard which specifies the test board and the pin loading.

**Table 72. EMI characteristics**

<b>Symbol</b>	<b>Parameter</b>	<b>Conditions</b>	<b>Monitored frequency band</b>	<b>Max vs. [<math>f_{HSE}/f_{HCLK}</math>]</b>	<b>Unit</b>
				<b>8 MHz / 120 MHz</b>	
$S_{EMI}$	Peak level	$V_{DD} = 3.6 \text{ V}$ , $T_A = 25^\circ\text{C}$ , UFBGA169 package compliant with IEC 61967-2	0.1 MHz to 30 MHz	-2	dB $\mu$ V
			30 MHz to 130 MHz	3	
			130 MHz to 1 GHz	10	
			1 GHz to 2 GHz	8	
			EMI Level	3	

### 6.3.15 Electrical sensitivity characteristics

Based on three different tests (ESD, LU) using specific measurement methods, the device is stressed in order to determine its performance in terms of electrical sensitivity.

#### Electrostatic discharge (ESD)

Electrostatic discharges (a positive then a negative pulse separated by 1 second) are applied to the pins of each sample according to each pin combination. The sample size depends on the number of supply pins in the device (3 parts  $\times$  (n+1) supply pins). This test conforms to the ANSI/JEDEC standard.

**Table 73. ESD absolute maximum ratings**

<b>Symbol</b>	<b>Ratings</b>	<b>Conditions</b>	<b>Class</b>	<b>Maximum value<sup>(1)</sup></b>	<b>Unit</b>
$V_{ESD(HBM)}$	Electrostatic discharge voltage (human body model)	$T_A = +25^\circ\text{C}$ , conforming to ANSI/ESDA/JEDEC JS-001	2	2000	V
$V_{ESD(CDM)}$	Electrostatic discharge voltage (charge device model)	$T_A = +25^\circ\text{C}$ , conforming to ANSI/ESD STM5.3.1			

1. Guaranteed by characterization results.

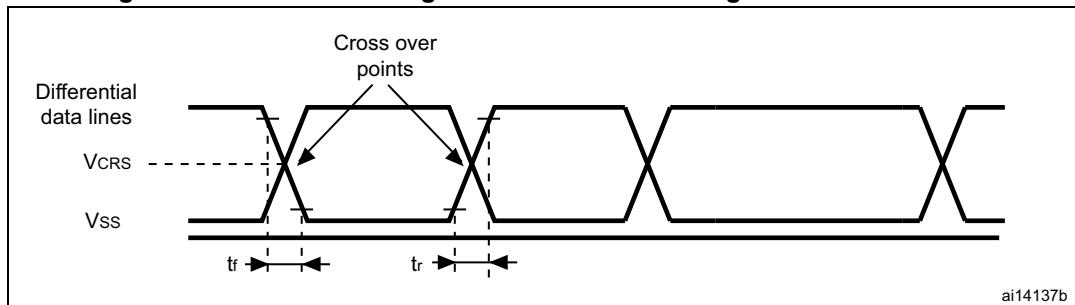
Table 78. I/O AC characteristics<sup>(1)(2)</sup> (continued)

Speed	Symbol	Parameter	Conditions	Min	Max	Unit
10	Fmax	Maximum frequency	C=50 pF, 2.7 V≤V <sub>DDIOx</sub> ≤3.6 V	-	50	MHz
			C=50 pF, 1.62 V≤V <sub>DDIOx</sub> ≤2.7 V	-	25	
			C=50 pF, 1.08 V≤V <sub>DDIOx</sub> ≤1.62 V	-	5	
			C=10 pF, 2.7 V≤V <sub>DDIOx</sub> ≤3.6 V	-	100 <sup>(3)</sup>	
			C=10 pF, 1.62 V≤V <sub>DDIOx</sub> ≤2.7 V	-	37.5	
			C=10 pF, 1.08 V≤V <sub>DDIOx</sub> ≤1.62 V	-	5	
	Tr/Tf	Output rise and fall time	C=50 pF, 2.7 V≤V <sub>DDIOx</sub> ≤3.6 V	-	5.8	ns
			C=50 pF, 1.62 V≤V <sub>DDIOx</sub> ≤2.7 V	-	11	
			C=50 pF, 1.08 V≤V <sub>DDIOx</sub> ≤1.62 V	-	28	
			C=10 pF, 2.7 V≤V <sub>DDIOx</sub> ≤3.6 V	-	2.5	
			C=10 pF, 1.62 V≤V <sub>DDIOx</sub> ≤2.7 V	-	5	
			C=10 pF, 1.08 V≤V <sub>DDIOx</sub> ≤1.62 V	-	12	
11	Fmax	Maximum frequency	C=30 pF, 2.7 V≤V <sub>DDIOx</sub> ≤3.6 V	-	120 <sup>(3)</sup>	MHz
			C=30 pF, 1.62 V≤V <sub>DDIOx</sub> ≤2.7 V	-	50	
			C=30 pF, 1.08 V≤V <sub>DDIOx</sub> ≤1.62 V	-	10	
			C=10 pF, 2.7 V≤V <sub>DDIOx</sub> ≤3.6 V	-	180 <sup>(3)</sup>	
			C=10 pF, 1.62 V≤V <sub>DDIOx</sub> ≤2.7 V	-	75	
			C=10 pF, 1.08 V≤V <sub>DDIOx</sub> ≤1.62 V	-	10	
	Tr/Tf	Output rise and fall time	C=30 pF, 2.7 V≤V <sub>DDIOx</sub> ≤3.6 V	-	3.3	ns
			C=30 pF, 1.62 V≤V <sub>DDIOx</sub> ≤2.7 V	-	6	
			C=30 pF, 1.08 V≤V <sub>DDIOx</sub> ≤1.62 V	-	16	
Fm+	Fmax	Maximum frequency	C=50 pF, 1.6 V≤V <sub>DDIOx</sub> ≤3.6 V	-	1	MHz
	Tf	Output fall time <sup>(4)</sup>		-	5	ns

1. The I/O speed is configured using the OSPEEDRy[1:0] bits. The Fm+ mode is configured in the SYSCFG\_CFGR1 register. Refer to the RM0351 reference manual for a description of GPIO Port configuration register.
2. Guaranteed by design.
3. This value represents the I/O capability but the maximum system frequency is limited to 80 MHz.
4. The fall time is defined between 70% and 30% of the output waveform accordingly to I<sup>2</sup>C specification.

1. Guaranteed by design.
2. The I/O analog switch voltage booster is enable when  $V_{DDA} < 2.4$  V (BOOSTEN = 1 in the SYSCFG\_CFGR1 when  $V_{DDA} < 2.4$  V). It is disable when  $V_{DDA} \geq 2.4$  V.
3. Fast channels are: PC0, PC1, PC2, PC3, PA0.
4. Slow channels are: all ADC inputs except the fast channels.

Figure 49. USB OTG timings – definition of data signal rise and fall time



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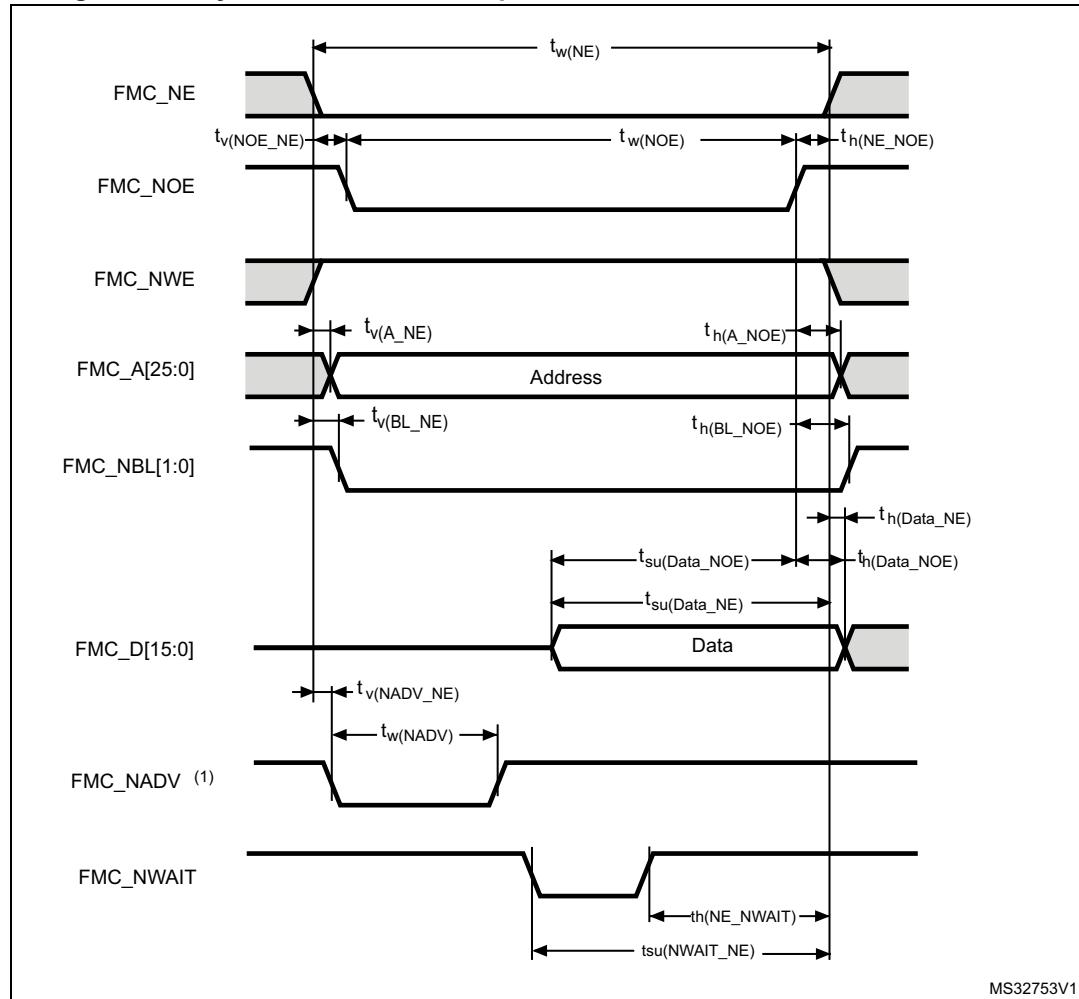
Table 104. USB OTG electrical characteristics<sup>(1)</sup>

Driver characteristics						
Symbol	Parameter	Conditions	Min	Max	Unit	
$t_{rLS}$	Rise time in LS <sup>(2)</sup>	$C_L = 200 \text{ to } 600 \text{ pF}$	75	300	ns	
$t_{fLS}$	Fall time in LS <sup>(2)</sup>					
$t_{rfmLS}$	Rise/ fall time matching in LS	$t_r / t_f$	80	125	%	
$t_{rFS}$	Rise time in FS <sup>(2)</sup>	$C_L = 50 \text{ pF}$				
$t_{fFS}$	Fall time in FS <sup>(2)</sup>	$C_L = 50 \text{ pF}$	4	20	ns	
$t_{rfmFS}$	Rise/ fall time matching in FS	$t_r / t_f$	90	111	%	
$V_{CRS}$	Output signal crossover voltage (LS/FS)	-	1.3	2.0	V	
$Z_{DRV}$	Output driver impedance <sup>(3)</sup>	Driving high or low	28	44	$\Omega$	

1. Guaranteed by design
2. Measured from 10% to 90% of the data signal. For more detailed informations, please refer to USB Specification - Chapter 7 (version 2.0).
3. No external termination series resistors are required on DP (D+) and DM (D-) pins since the matching impedance is included in the embedded driver.

Table 105. USB BCD DC electrical characteristics<sup>(1)</sup>

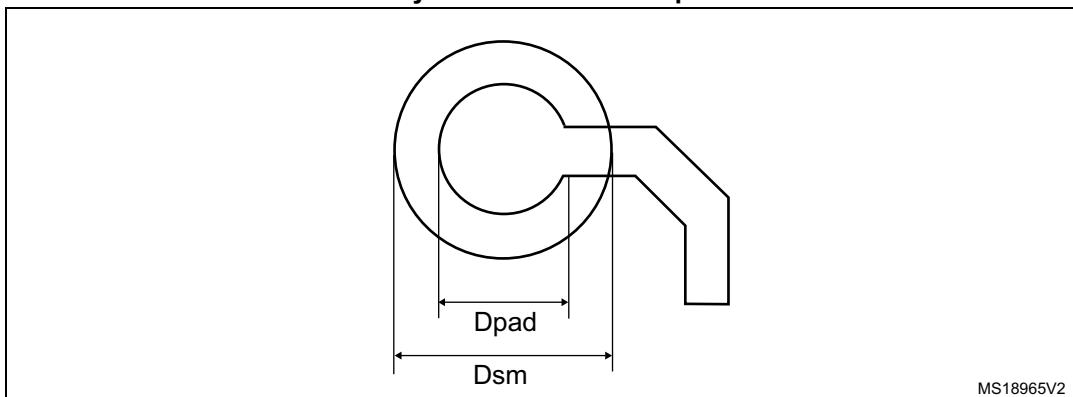
Driver characteristics						
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$I_{DD(USBBCD)}$	Primary detection mode consumption	-	-	-	300	$\mu\text{A}$
	Secondary detection mode consumption	-	-	-		
RDAT_LKG	Data line leakage resistance	-	300	-	-	$\text{k}\Omega$
VDAT_LKG	Data line leakage voltage	-	0.0	-	3.6	V
RDCP_DAT	Dedicated charging port resistance across D+/D-	-	-	-	200	$\Omega$
VLGC_HI	Logic high	-	2.0	-	3.6	V
VLGC_LOW	Logic low	-	-	-	0.8	V

**Figure 50. Asynchronous non-multiplexed SRAM/PSRAM/NOR read waveforms**

**Table 127. UFBGA169 - 169-ball, 7 x 7 mm, 0.50 mm pitch, ultra fine pitch ball grid array package mechanical data (continued)**

Symbol	millimeters			inches <sup>(1)</sup>		
	Min.	Typ.	Max.	Min.	Typ.	Max.
b	0.230	0.280	0.330	0.0091	0.0110	0.0130
D	6.950	7.000	7.050	0.2736	0.2756	0.2776
D1	5.950	6.000	6.050	0.2343	0.2362	0.2382
E	6.950	7.000	7.050	0.2736	0.2756	0.2776
E1	5.950	6.000	6.050	0.2343	0.2362	0.2382
e	-	0.500	-	-	0.0197	-
F	0.450	0.500	0.550	0.0177	0.0197	0.0217
ddd	-	-	0.100	-	-	0.0039
eee	-	-	0.150	-	-	0.0059
fff	-	-	0.050	-	-	0.0020

1. Values in inches are converted from mm and rounded to 4 decimal digits.

**Figure 73. UFBGA169 - 169-ball, 7 x 7 mm, 0.50 mm pitch, ultra fine pitch ball grid array recommended footprint****Table 128. UFBGA169 recommended PCB design rules (0.5 mm pitch BGA)**

Dimension	Recommended values
Pitch	0.5 mm
Dpad	0.27 mm
Dsm	0.35 mm typ. (depends on the soldermask registration tolerance)
Solder paste	0.27 mm aperture diameter.

**Note:** Non-solder mask defined (NSMD) pads are recommended.

**Note:** 4 to 6 mils solder paste screen printing process.